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12 Output Buffer for 2 DDR and 3 SRAM DIMMS

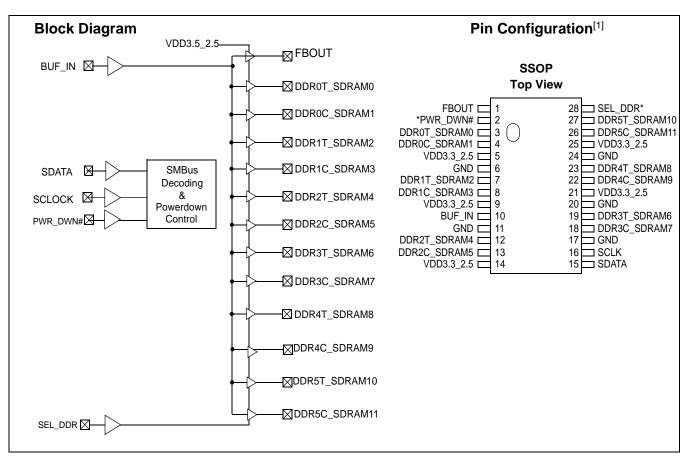
Features

- One input to 12 output buffer/drivers
- Supports up to 2 DDR DIMMs or 3 SDRAM DIMMS
- One additional output for feedback
- SMBus interface for individual output control
- Low skew outputs (< 100 ps)
- Supports 266 MHz and 333 MHz DDR SDRAM
- Dedicated pin for power management support
- Space-saving 28-pin SSOP package

Functional Description

The W256 is a 3.3V/2.5V buffer designed to distribute high-speed clocks in PC applications. The part has 12 outputs. Designers can configure these outputs to support 3 unbuffered standard SDRAM DIMMs and 2 DDR DIMMs. The W256 can be used in conjunction with the W250-02 or similar clock synthesizer for the VIA Pro 266 chipset.

The W256 also includes an SMBus interface which can enable or disable each output clock. On power-up, all output clocks are enabled (internal pull-up).



Note:

1. Internal 100K pull-up resistors present on inputs marked with *. Design should not rely solely on internal pull-up resistor to set I/O pins HIGH.



Pin Summary

Name	Pins	Description	
SEL_DDR	28	Input to configure for DDR-ONLY mode or STANDARD SDRAM mode. 1 = DDR-ONLY mode. 0 = STANDARD SDRAM mode. When SEL_DDR is pulled HIGH or configured for DDR-ONLY mode, all the buffers will be configured as DDR outputs. Connect VDD3.3_2.5 to a 2.5V power supply in DDR-ONLY mode. When SEL_DDR is pulled LOW or configured for STANDARD SDRAM output, all the buffers will be configured as STANDARD SDRAM outputs. Connect VDD3.3_2.5 to a 3.3V power supply in STANDARD SDRAM mode.	
SCLK	16	SMBus clock input.	
SDATA	15	SMBus data input.	
BUF_IN	10	Reference input from chipset . 2.5V input for DDR-ONLY mode; 3.3V input for STANDARD SDRAM mode.	
FBOUT	1	Feedback clock for chipset. Output voltage depends on VDD3.3_2.5V.	
PWR_DWN#	2	Active LOW input to enable Power Down mode; all outputs will be pulled LOW.	
DDR[0:5]T_SDRAM [0,2,4,6,8,10]	3, 7, 12, 19, 23, 27	Clock outputs . These outputs provide copies of BUF_IN. Voltage swing depends on VDD3.3_2.5 power supply.	
DDR[0:5]C_SDRAM [1,3,5,7,9, 11]	4, 8, 13, 18, 22, 26		
VDD3.3_2.5	5, 9, 14, 21, 25	Connect to 2.5V power supply when W256 is configured for DDR-ONLY mode . Connect to 3.3V power supply, when W256 is configured for standard SDRAM mode.	
GND	6, 11, 17, 20, 24	Ground.	



Serial Configuration Map

• The Serial bits will be read by the clock driver in the following order:

Byte 0 — Bits 7, 6, 5, 4, 3, 2, 1, 0 Byte 1 — Bits 7, 6, 5, 4, 3, 2, 1, 0 .-

- Byte N Bits 7, 6, 5, 4, 3, 2, 1, 0
- Reserved and unused bits should be programmed to "0".
- SMBus Address for the W256 is:

Table 1.

A6	A5	A4	A3	A2	A1	A0	R/W
1	1	0	1	0	0	1	

Byte 6: Outputs Active/Inactive Register (1 = Active, 0 = Inactive), Default = Active

Bit	Pin #	Description	Default
Bit 7	-	Reserved, drive to 0	0
Bit 6	-	Reserved, drive to 0	0
Bit 5	-	Reserved, drive to 0	0
Bit 4	1	FBOUT	1
Bit 3	27, 26	DDR5T_SDRAM10, DDR5C_S- DRAM11	1
Bit 2	-	Reserved, drive to 0	1
Bit 1	23, 22	DDR4T_SDRAM8, DDR4C_S- DRAM9	1
Bit 0	-	Reserved, drive to 0	1

Byte 7: Outputs Active/Inactive Register (1 = Active, 0 = Inactive), Default = Active

•		•	
Bit	Pin #	Description	Default
Bit 7	-	Reserved, drive to 0	1
Bit 6	19, 18	DDR3T_SDRAM6, DDR3C_SDRAM7	1
Bit 5	12, 13	DDR2T_SDRAM4, DDR2C_SDRAM5	1
Bit 4	-	Reserved, drive to 0	1
Bit 3	-	Reserved, drive to 0	1
Bit 2	7, 8	DDR1T_SDRAM2, DDR1C_SDRAM3	1
Bit 1	-	Reserved, drive to 0	1
Bit 0	3, 4	DDR0T_SDRAM0, DDR0C_SDRAM1	1



Maximum Ratings

Supply Voltage to Ground Potential0.5 to +7.0V	
DC Input Voltage (except BUF_IN)0.5V to $V_{\text{DD}}\text{+}0.5$	
Storage Temperature65°C to +150°C	
Static Discharge Voltage>2000V (per MIL-STD-883, Method 3015)	

Operating Conditions^[2]

Parameter	Description	Min.	Тур.	Max.	Unit
V _{DD3.3}	Supply Voltage	3.135		3.465	V
V _{DD2.5}	Supply Voltage	2.375		2.625	V
T _A	Operating Temperature (Ambient Temperature)	0		70	°C
C _{OUT} Output Capacitance			6		pF
C _{IN}	Input Capacitance		5		pF

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	Min.	Тур.	Max.	Unit
V _{IL}	Input LOW Voltage	For all pins except SMBus			0.8	V
V _{IH}	Input HIGH Voltage		2.0			V
IIL	Input LOW Current	$V_{IN} = 0V$			50	μΑ
I _{IH}	Input HIGH Current	$V_{IN} = V_{DD}$			50	μΑ
I _{OH}	Output HIGH Current	V _{DD} = 2.375V V _{OUT} = 1V	-18	-32		mA
I _{OL}	Output LOW Current	V _{DD} = 2.375V V _{OUT} = 1.2V	26	35		mA
V _{OL}	Output LOW Voltage ^[3]	I _{OL} = 12 mA, V _{DD} = 2.375V			0.6	V
V _{OH}	Output HIGH Voltage ^[3]	$I_{OH} = -12 \text{ mA}, V_{DD} = 2.375 \text{ V}$	1.7			V
I _{DD}	Supply Current ^[3] (DDR-Only mode)	Unloaded outputs, 133 MHz			400	mA
I _{DD}	Supply Current (DDR-Only mode)	Loaded outputs, 133 MHz			500	mA
I _{DDS}	Supply Current	PWR_DWN# = 0			100	μΑ
V _{OUT}	Output Voltage Swing	See Test Circuity (Refer to Figure 1)	0.7		V _{DD} + 0.6	V
V _{OC}	Output Crossing Voltage		(V _{DD} /2) -0.1	V _{DD} /2	(V _{DD} /2) +0.1	V
IN _{DC}	Input Clock Duty Cycle		48		52	%

Notes:

Multiple Supplies: The voltage on any input or I/O pin cannot exceed the power pin during power-up. Power supply sequencing is NOT required.
Parameter is guaranteed by design and characterization. Not 100% tested in production.

Switching Characteristics^[4]

Parameter	Name	Test Conditions	Min.	Тур.	Max.	Unit
_	Operating Frequency		66		180	MHz
	Duty Cycle ^[4,5] = $t_2 \div t_1$	Measured at 1.4V for 3.3V outputs Measured at VDD/2 for 2.5V outputs.	IN _{DC} -5%		IN _{DC} +5%	%
t ₃	SDRAM Rising Edge Rate ^[4]	Measured between 0.4V and 2.4V	1.0		2.50	V/ns
t ₄	SDRAM Falling Edge Rate ^[4]	Measured between 2.4V and 0.4V	1.0		2.50	V/ns

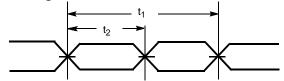


Switching Characteristics^[4]

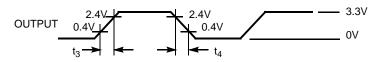
Parameter	Name	Test Conditions	Min.	Тур.	Max.	Unit
t _{3d}	DDR Rising Edge Rate ^[4]	Measured between 20% to 80% of output (Refer to <i>Figure 1</i>)	0.5		1.50	V/ns
t _{4d}	DDR Falling Edge Rate ^[4]	Measured between 20% to 80% of output (Refer to <i>Figure 1</i>)	0.5		1.50	V/ns
t ₅	Output to Output Skew ^[4]	All outputs equally loaded			100	ps
t ₆	Output t4o Output Skew for SDRAM ^[2]	All outputs equally loaded			150	ps
t ₇	SDRAM Buffer HH Prop. Delay ^[4]	Input edge greater than 1 V/ns	5		10	ns
t ₈	SDRAM Buffer LLProp. Delay ^[4]	Input edge greater than 1 V/ns	5		10	ns

Switching Waveforms

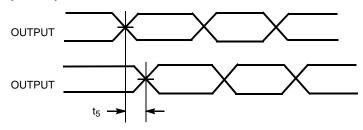
Duty Cycle Timing



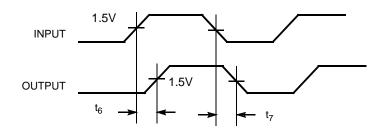
All Outputs Rise/Fall Time



Output-Output Skew



SDRAM Buffer HH and LL Propagation Delay



Notes:

All parameters specified with loaded outputs.
Duty cycle of input clock is 50%. Rising and falling edge rate is greater than 1V/ns.



Figure 1 shows the differential clock directly terminated by a 120 Ω resistor.

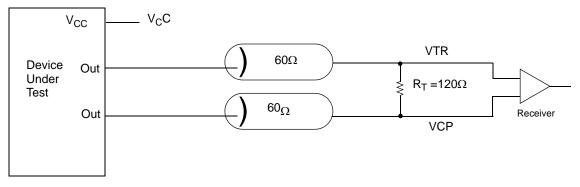
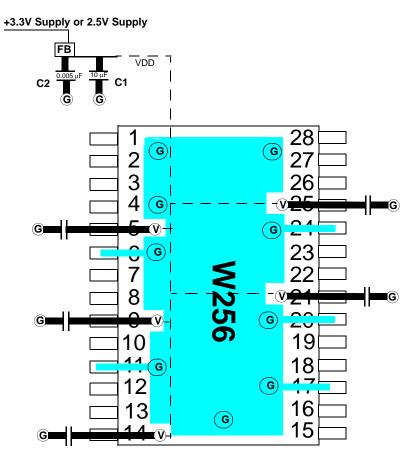


Figure 1. Differential Signal Using Direct Termination Resistor

Layout Example Single Voltage



FB = Dale ILB1206 - 300 (300Ω @ 100 MHz)

Cermaic Caps C1 = $10-22 \ \mu F$ C2 = $0.005 \ \mu F$

(G) = VIA to GND plane layer (V) =VIA to respective supply plane layer

Note: Each supply plane or strip should have a ferrite bead and capacitors All bypass caps = 0.1 μF ceramic

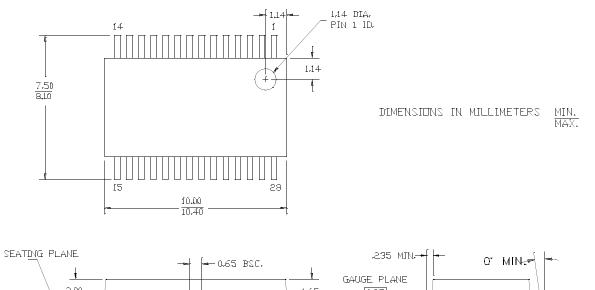


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Ordering Information

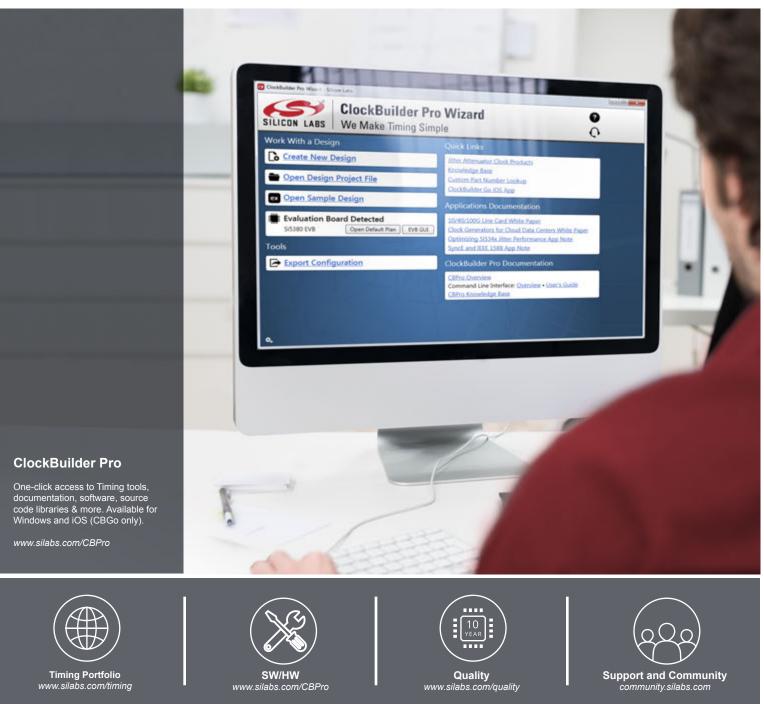
Ordering Code	Package Type	Operating Range
W256H	28-pin SSOP	Commercial
W256HT	28-pin SSOP – Tape and Reel	Commercial
Lead Free		
CYW256OXC	28-pin SSOP	Commercial
CYW256OXCT	28-pin SSOP – Tape and Reel	Commercial

Package Drawings and Dimension



28-Lead (5.3 mm) Shrunk Small Outline Package O28

SEATING PLANE 2.00 MAX, + 0.05 0.21 0.22 0.22 0.22 0.22 0.22 0.22 0.25 0.25 0.25 1.25 REF, + 0.55 0.250.25



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